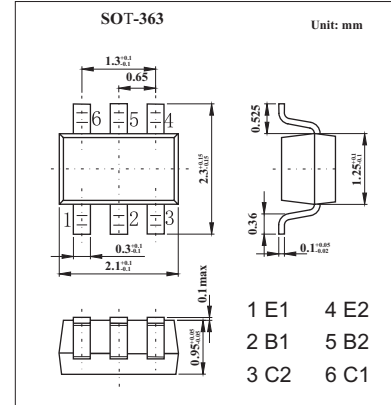
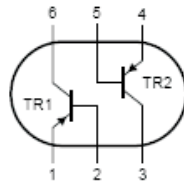


KC856S(BC856S)

■ **Features**

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors.



■ **Absolute Maximum Ratings** Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	-80	V
Collector-Emitter Voltage	V _{CE0}	-65	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current - Continuous	I _c	-100	mA
Power Dissipation	P _D	200	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	416	°C/W
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

■ **Electrical Characteristics** Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-Cutoff Current	I _{CBO}	V _{CB} = -30 V, I _E = 0			-15	nA
		V _{CB} = -30 V, I _E = 0, T _A = 150°C			-5.0	μA
Emitter- cutoff current	I _{EBO}	I _C =0, V _{EB} =-5V			-100	nA
DC Current Gain	h _{FE}	I _C = -2.0 mA, V _{CE} = -5.0 V	110			
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = -10 mA, I _B = -0.5 mA			-100	mV
		I _C = -100 mA, I _B = -5.0 mA			-300	mV
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C = -10 mA, I _B =-0.5mA		700		mV
Output Capacitance	C _{ob}	V _{CB} = -10 V, f = 1.0 MHz			2.5	pF
Transistion frequency	f _T	I _C = -10 mA, V _{CE} = -5.0V, f = 100 mHz	100			MHz

■ **Marking**

Marking	5F
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